



Welcome to [E-XFL.COM](https://www.e-xfl.com)

Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	280
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe1500-2fgg484

Advanced Architecture

The proprietary ProASIC3E architecture provides granularity comparable to standard-cell ASICs. The ProASIC3E device consists of five distinct and programmable architectural features (Figure 1-1 on page 3):

- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory
- Extensive CCCs and PLLs
- Pro I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the ProASIC3E core tile as either a three-input lookup table (LUT) equivalent or as a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the ProASIC family of third-generation architecture Flash FPGAs. VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

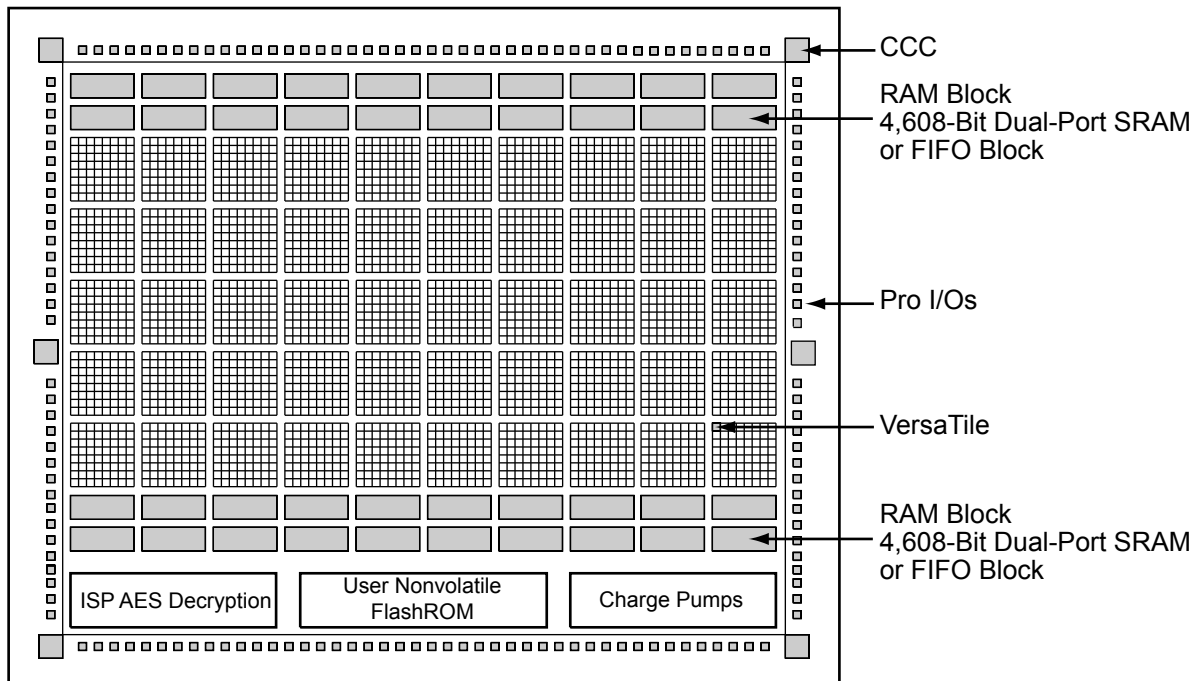


Figure 1-1 • ProASIC3E Device Architecture Overview

Combinatorial Cells Contribution— P_{C-CELL}

$$P_{C-CELL} = N_{C-CELL} * \alpha_1 / 2 * PAC7 * F_{CLK}$$

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-11 on page 2-11](#).

F_{CLK} is the global clock signal frequency.

Routing Net Contribution— P_{NET}

$$P_{NET} = (N_{S-CELL} + N_{C-CELL}) * \alpha_1 / 2 * PAC8 * F_{CLK}$$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-11 on page 2-11](#).

F_{CLK} is the global clock signal frequency.

I/O Input Buffer Contribution— P_{INPUTS}

$$P_{INPUTS} = N_{INPUTS} * \alpha_2 / 2 * PAC9 * F_{CLK}$$

N_{INPUTS} is the number of I/O input buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in [Table 2-11 on page 2-11](#).

F_{CLK} is the global clock signal frequency.

I/O Output Buffer Contribution— $P_{OUTPUTS}$

$$P_{OUTPUTS} = N_{OUTPUTS} * \alpha_2 / 2 * \beta_1 * PAC10 * F_{CLK}$$

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in [Table 2-11 on page 2-11](#).

β_1 is the I/O buffer enable rate—guidelines are provided in [Table 2-12 on page 2-11](#).

F_{CLK} is the global clock signal frequency.

RAM Contribution— P_{MEMORY}

$$P_{MEMORY} = PAC11 * N_{BLOCKS} * F_{READ-CLOCK} * \beta_2 + PAC12 * N_{BLOCK} * F_{WRITE-CLOCK} * \beta_3$$

N_{BLOCKS} is the number of RAM blocks used in the design.

$F_{READ-CLOCK}$ is the memory read clock frequency.

β_2 is the RAM enable rate for read operations—guidelines are provided in [Table 2-12 on page 2-11](#).

$F_{WRITE-CLOCK}$ is the memory write clock frequency.

β_3 is the RAM enable rate for write operations—guidelines are provided in [Table 2-12 on page 2-11](#).

PLL Contribution— P_{PLL}

$$P_{PLL} = PAC13 + PAC14 * F_{CLKOUT}$$

F_{CLKOUT} is the output clock frequency.¹

1. The PLL dynamic contribution depends on the input clock frequency, the number of output clock signals generated by the PLL, and the frequency of each output clock. If a PLL is used to generate more than one output clock, include each output clock in the formula by adding its corresponding contribution ($PAC14 * F_{CLKOUT}$ product) to the total PLL contribution.

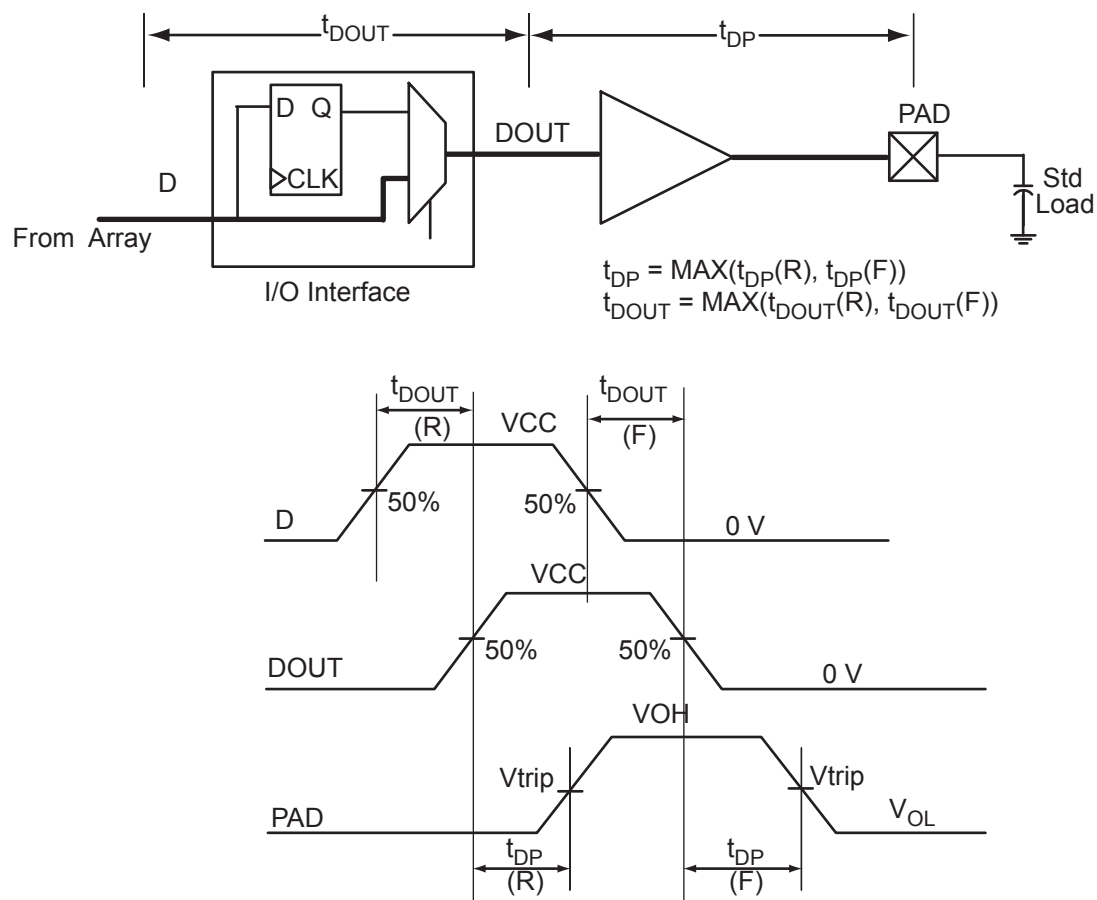


Figure 2-4 • Output Buffer Model and Delays (example)

Table 2-28 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
12 mA	Std.	0.66	6.03	0.04	1.20	1.57	0.43	6.14	5.02	3.28	3.47	8.37	7.26	ns
	–1	0.56	5.13	0.04	1.02	1.33	0.36	5.22	4.27	2.79	2.95	7.12	6.17	ns
	–2	0.49	4.50	0.03	0.90	1.17	0.32	4.58	3.75	2.45	2.59	6.25	5.42	ns
16 mA	Std.	0.66	5.62	0.04	1.20	1.57	0.43	5.72	4.72	3.32	3.58	7.96	6.96	ns
	–1	0.56	4.78	0.04	1.02	1.33	0.36	4.87	4.02	2.83	3.04	6.77	5.92	ns
	–2	0.49	4.20	0.03	0.90	1.17	0.32	4.27	3.53	2.48	2.67	5.94	5.20	ns
24 mA	Std.	0.66	5.24	0.04	1.20	1.57	0.43	5.34	4.69	3.39	3.96	7.58	6.93	ns
	–1	0.56	4.46	0.04	1.02	1.33	0.36	4.54	3.99	2.88	3.37	6.44	5.89	ns
	–2	0.49	3.92	0.03	0.90	1.17	0.32	3.99	3.50	2.53	2.96	5.66	5.17	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

Timing Characteristics

Table 2-35 • 2.5 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	8.82	0.04	1.51	1.66	0.43	8.13	8.82	2.72	2.29	10.37	11.05	ns
	–1	0.56	7.50	0.04	1.29	1.41	0.36	6.92	7.50	2.31	1.95	8.82	9.40	ns
	–2	0.49	6.58	0.03	1.13	1.24	0.32	6.07	6.58	2.03	1.71	7.74	8.25	ns
8 mA	Std.	0.66	5.27	0.04	1.51	1.66	0.43	5.27	5.27	3.10	3.03	7.50	7.51	ns
	–1	0.56	4.48	0.04	1.29	1.41	0.36	4.48	4.48	2.64	2.58	6.38	6.38	ns
	–2	0.49	3.94	0.03	1.13	1.24	0.32	3.93	3.94	2.32	2.26	5.60	5.61	ns
12 mA	Std.	0.66	3.74	0.04	1.51	1.66	0.43	3.81	3.49	3.37	3.49	6.05	5.73	ns
	–1	0.56	3.18	0.04	1.29	1.41	0.36	3.24	2.97	2.86	2.97	5.15	4.87	ns
	–2	0.49	2.80	0.03	1.13	1.24	0.32	2.85	2.61	2.51	2.61	4.52	4.28	ns
16 mA	Std.	0.66	3.53	0.04	1.51	1.66	0.43	3.59	3.12	3.42	3.62	5.83	5.35	ns
	–1	0.56	3.00	0.04	1.29	1.41	0.36	3.06	2.65	2.91	3.08	4.96	4.55	ns
	–2	0.49	2.63	0.03	1.13	1.24	0.32	2.68	2.33	2.56	2.71	4.35	4.00	ns
24 mA	Std.	0.66	3.26	0.04	1.51	1.66	0.43	3.32	2.48	3.49	4.11	5.56	4.72	ns
	–1	0.56	2.77	0.04	1.29	1.41	0.36	2.83	2.11	2.97	3.49	4.73	4.01	ns
	–2	0.49	2.44	0.03	1.13	1.24	0.32	2.48	1.85	2.61	3.07	4.15	3.52	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

Timing Characteristics

Table 2-39 • 1.8 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.7\text{ V}$

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	12.10	0.04	1.45	1.91	0.43	9.59	12.10	2.78	1.64	11.83	14.34	ns
	–1	0.56	10.30	0.04	1.23	1.62	0.36	8.16	10.30	2.37	1.39	10.06	12.20	ns
	–2	0.49	9.04	0.03	1.08	1.42	0.32	7.16	9.04	2.08	1.22	8.83	10.71	ns
4 mA	Std.	0.66	7.05	0.04	1.45	1.91	0.43	6.20	7.05	3.25	2.86	8.44	9.29	ns
	–1	0.56	6.00	0.04	1.23	1.62	0.36	5.28	6.00	2.76	2.44	7.18	7.90	ns
	–2	0.49	5.27	0.03	1.08	1.42	0.32	4.63	5.27	2.43	2.14	6.30	6.94	ns
6 mA	Std.	0.66	4.52	0.04	1.45	1.91	0.43	4.47	4.52	3.57	3.47	6.70	6.76	ns
	–1	0.56	3.85	0.04	1.23	1.62	0.36	3.80	3.85	3.04	2.95	5.70	5.75	ns
	–2	0.49	3.38	0.03	1.08	1.42	0.32	3.33	3.38	2.66	2.59	5.00	5.05	ns
8 mA	Std.	0.66	4.12	0.04	1.45	1.91	0.43	4.20	3.99	3.63	3.62	6.43	6.23	ns
	–1	0.56	3.51	0.04	1.23	1.62	0.36	3.57	3.40	3.09	3.08	5.47	5.30	ns
	–2	0.49	3.08	0.03	1.08	1.42	0.32	3.14	2.98	2.71	2.71	4.81	4.65	ns
12 mA	Std.	0.66	3.80	0.04	1.45	1.91	0.43	3.87	3.09	3.73	4.24	6.10	5.32	ns
	–1	0.56	3.23	0.04	1.23	1.62	0.36	3.29	2.63	3.18	3.60	5.19	4.53	ns
	–2	0.49	2.83	0.03	1.08	1.42	0.32	2.89	2.31	2.79	3.16	4.56	3.98	ns
16 mA	Std.	0.66	3.80	0.04	1.45	1.91	0.43	3.87	3.09	3.73	4.24	6.10	5.32	ns
	–1	0.56	3.23	0.04	1.23	1.62	0.36	3.29	2.63	3.18	3.60	5.19	4.53	ns
	–2	0.49	2.83	0.03	1.08	1.42	0.32	2.89	2.31	2.79	3.16	4.56	3.98	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

Timing Characteristics

Table 2-43 • 1.5 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.4\text{ V}$

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	8.53	0.04	1.70	2.14	0.43	7.26	8.53	3.39	2.79	9.50	10.77	ns
	–1	0.56	7.26	0.04	1.44	1.82	0.36	6.18	7.26	2.89	2.37	8.08	9.16	ns
	–2	0.49	6.37	0.03	1.27	1.60	0.32	5.42	6.37	2.53	2.08	7.09	8.04	ns
4 mA	Std.	0.66	5.41	0.04	1.70	2.14	0.43	5.22	5.41	3.75	3.48	7.45	7.65	ns
	–1	0.56	4.60	0.04	1.44	1.82	0.36	4.44	4.60	3.19	2.96	6.34	6.50	ns
	–2	0.49	4.04	0.03	1.27	1.60	0.32	3.89	4.04	2.80	2.60	5.56	5.71	ns
6 mA	Std.	0.66	4.80	0.04	1.70	2.14	0.43	4.89	4.75	3.83	3.67	7.13	6.98	ns
	–1	0.56	4.09	0.04	1.44	1.82	0.36	4.16	4.04	3.26	3.12	6.06	5.94	ns
	–2	0.49	3.59	0.03	1.27	1.60	0.32	3.65	3.54	2.86	2.74	5.32	5.21	ns
8 mA	Std.	0.66	4.42	0.04	1.70	2.14	0.43	4.50	3.62	3.96	4.37	6.74	5.86	ns
	–1	0.56	3.76	0.04	1.44	1.82	0.36	3.83	3.08	3.37	3.72	5.73	4.98	ns
	–2	0.49	3.30	0.03	1.27	1.60	0.32	3.36	2.70	2.96	3.27	5.03	4.37	ns
12 mA	Std.	0.66	4.42	0.04	1.70	2.14	0.43	4.50	3.62	3.96	4.37	6.74	5.86	ns
	–1	0.56	3.76	0.04	1.44	1.82	0.36	3.83	3.08	3.37	3.72	5.73	4.98	ns
	–2	0.49	3.30	0.03	1.27	1.60	0.32	3.36	2.70	2.96	3.27	5.03	4.37	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

Table 2-44 • 1.5 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.4\text{ V}$

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	14.11	0.04	1.70	2.14	0.43	14.37	13.14	3.40	2.68	16.61	15.37	ns
	–1	0.56	12.00	0.04	1.44	1.82	0.36	12.22	11.17	2.90	2.28	14.13	13.08	ns
	–2	0.49	10.54	0.03	1.27	1.60	0.32	10.73	9.81	2.54	2.00	12.40	11.48	ns
4 mA	Std.	0.66	11.23	0.04	1.70	2.14	0.43	11.44	9.87	3.77	3.36	13.68	12.10	ns
	–1	0.56	9.55	0.04	1.44	1.82	0.36	9.73	8.39	3.21	2.86	11.63	10.29	ns
	–2	0.49	8.39	0.03	1.27	1.60	0.32	8.54	7.37	2.81	2.51	10.21	9.04	ns
6 mA	Std.	0.66	10.45	0.04	1.70	2.14	0.43	10.65	9.24	3.84	3.55	12.88	11.48	ns
	–1	0.56	8.89	0.04	1.44	1.82	0.36	9.06	7.86	3.27	3.02	10.96	9.76	ns
	–2	0.49	7.81	0.03	1.27	1.60	0.32	7.95	6.90	2.87	2.65	9.62	8.57	ns
8 mA	Std.	0.66	10.02	0.04	1.70	2.14	0.43	10.20	9.23	3.97	4.22	12.44	11.47	ns
	–1	0.56	8.52	0.04	1.44	1.82	0.36	8.68	7.85	3.38	3.59	10.58	9.75	ns
	–2	0.49	7.48	0.03	1.27	1.60	0.32	7.62	6.89	2.97	3.15	9.29	8.56	ns
12 mA	Std.	0.66	10.02	0.04	1.70	2.14	0.43	10.20	9.23	3.97	4.22	12.44	11.47	ns
	–1	0.56	8.52	0.04	1.44	1.82	0.36	8.68	7.85	3.38	3.59	10.58	9.75	ns
	–2	0.49	7.48	0.03	1.27	1.60	0.32	7.62	6.89	2.97	3.15	9.29	8.56	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

HSTL Class II

High-Speed Transceiver Logic is a general-purpose high-speed 1.5 V bus standard (EIA/JESD8-6). ProASIC3E devices support Class II. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-63 • Minimum and Maximum DC Input and Output Levels

HSTL Class II	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA ²	μA ²
15 mA ³	−0.3	VREF − 0.1	VREF + 0.1	3.6	0.4	VCCI − 0.4	15	15	55	66	10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 85°C junction temperature.
3. Output drive strength is below JEDEC specification.

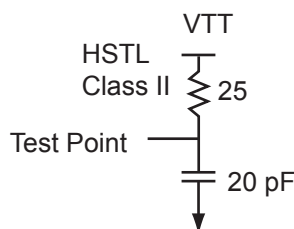


Figure 2-17 • AC Loading

Table 2-64 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)
VREF − 0.1	VREF + 0.1	0.75	0.75	0.75	20

Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.

Timing Characteristics

Table 2-65 • HSTL Class II

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 1.4 V, VREF = 0.75 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
Std.	0.66	3.02	0.04	2.12	0.43	3.08	2.71			5.32	4.95	ns
−1	0.56	2.57	0.04	1.81	0.36	2.62	2.31			4.52	4.21	ns
−2	0.49	2.26	0.03	1.59	0.32	2.30	2.03			3.97	3.70	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Table 2-78 • LVDS Minimum and Maximum DC Input and Output Levels

DC Parameter	Description	Min.	Typ.	Max.	Units
VCCI	Supply Voltage	2.375	2.5	2.625	V
VOL	Output Low Voltage	0.9	1.075	1.25	V
VOH	Output High Voltage	1.25	1.425	1.6	V
IOL ¹	Output Lower Current	0.65	0.91	1.16	mA
IOH ¹	Output High Current	0.65	0.91	1.16	mA
VI	Input Voltage	0		2.925	V
IIH ²	Input High Leakage Current			10	μA
IIL ²	Input Low Leakage Current			10	μA
VODIFF	Differential Output Voltage	250	350	450	mV
VOCM	Output Common Mode Voltage	1.125	1.25	1.375	V
VICM	Input Common Mode Voltage	0.05	1.25	2.35	V
VIDIFF	Input Differential Voltage ²	100	350		mV

Notes:

1. IOL/IOH defined by VODIFF/(Resistor Network).
2. Currents are measured at 85°C junction temperature.

Table 2-79 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)
1.075	1.325	Cross point	–

Note: *Measuring point = Vtrip. See [Table 2-15 on page 2-18](#) for a complete table of trip points.

Table 2-85 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OSUE}	Enable Setup Time for the Output Data Register	GG, HH
t_{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t_{OESUE}	Enable Setup Time for the Output Enable Register	KK, HH
t_{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t_{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

Note: *See Figure 2-26 on page 2-55 for more information.

Output Enable Register

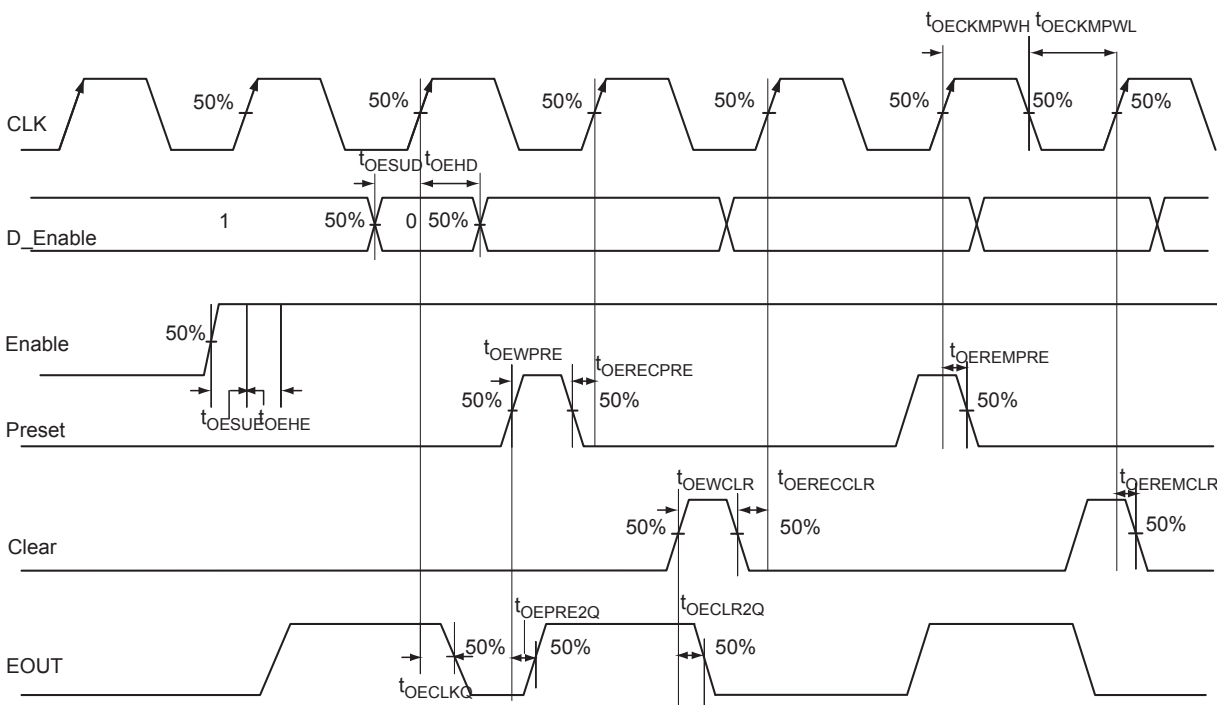


Figure 2-29 • Output Enable Register Timing Diagram

Timing Characteristics

Table 2-88 • Output Enable Register Propagation Delays

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.59	0.67	0.79	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.31	0.36	0.42	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	0.00	0.00	ns
t_{OESUE}	Enable Setup Time for the Output Enable Register	0.44	0.50	0.58	ns
t_{OEHE}	Enable Hold Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	0.67	0.76	0.89	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	0.67	0.76	0.89	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.22	0.25	0.30	ns
$t_{OEREMPRES}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.22	0.25	0.30	ns
t_{OEWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.22	0.25	0.30	ns
t_{OEWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.22	0.25	0.30	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.36	0.41	0.48	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

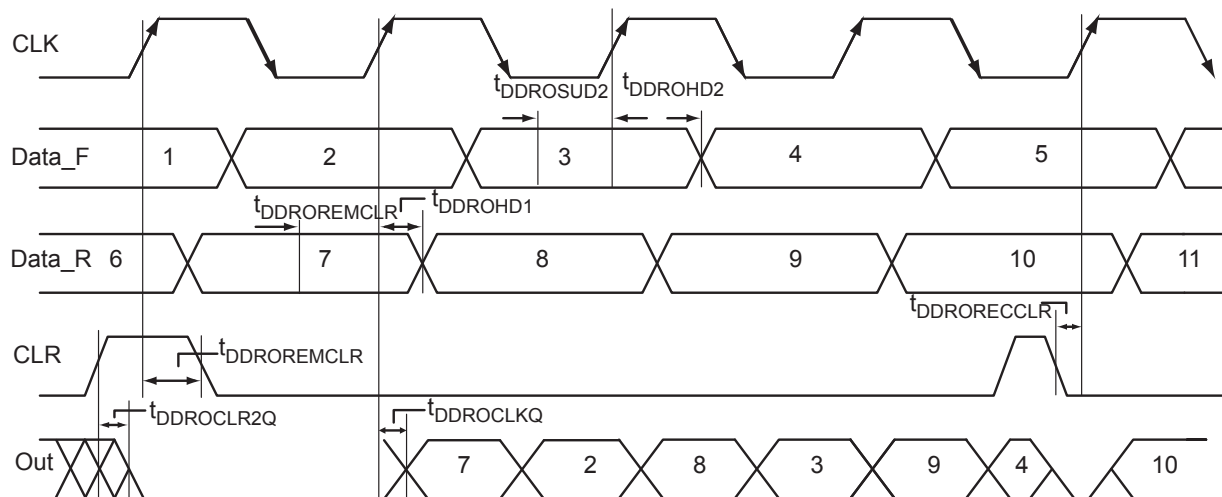


Figure 2-33 • Output DDR Timing Diagram

Timing Characteristics

Table 2-92 • Output DDR Propagation Delays

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{DDROCLKQ}	Clock-to-Out of DDR for Output DDR	0.70	0.80	0.94	ns
t_{DDROSUD1}	Data_F Data Setup for Output DDR	0.38	0.43	0.51	ns
t_{DDROSUD2}	Data_R Data Setup for Output DDR	0.38	0.43	0.51	ns
t_{DDROHD1}	Data_F Data Hold for Output DDR	0.00	0.00	0.00	ns
t_{DDROHD2}	Data_R Data Hold for Output DDR	0.00	0.00	0.00	ns
$t_{\text{DDROCLR2Q}}$	Asynchronous Clear-to-Out for Output DDR	0.80	0.91	1.07	ns
$t_{\text{DDROREMCLR}}$	Asynchronous Clear Removal Time for Output DDR	0.00	0.00	0.00	ns
$t_{\text{DDROECCLR}}$	Asynchronous Clear Recovery Time for Output DDR	0.22	0.25	0.30	ns
$t_{\text{DDROWCLR1}}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.22	0.25	0.30	ns
$t_{\text{DDROCKMPWH}}$	Clock Minimum Pulse Width High for the Output DDR	0.36	0.41	0.48	ns
$t_{\text{DDROCKMPWL}}$	Clock Minimum Pulse Width Low for the Output DDR	0.32	0.37	0.43	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	1404	1232	1048	MHz

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

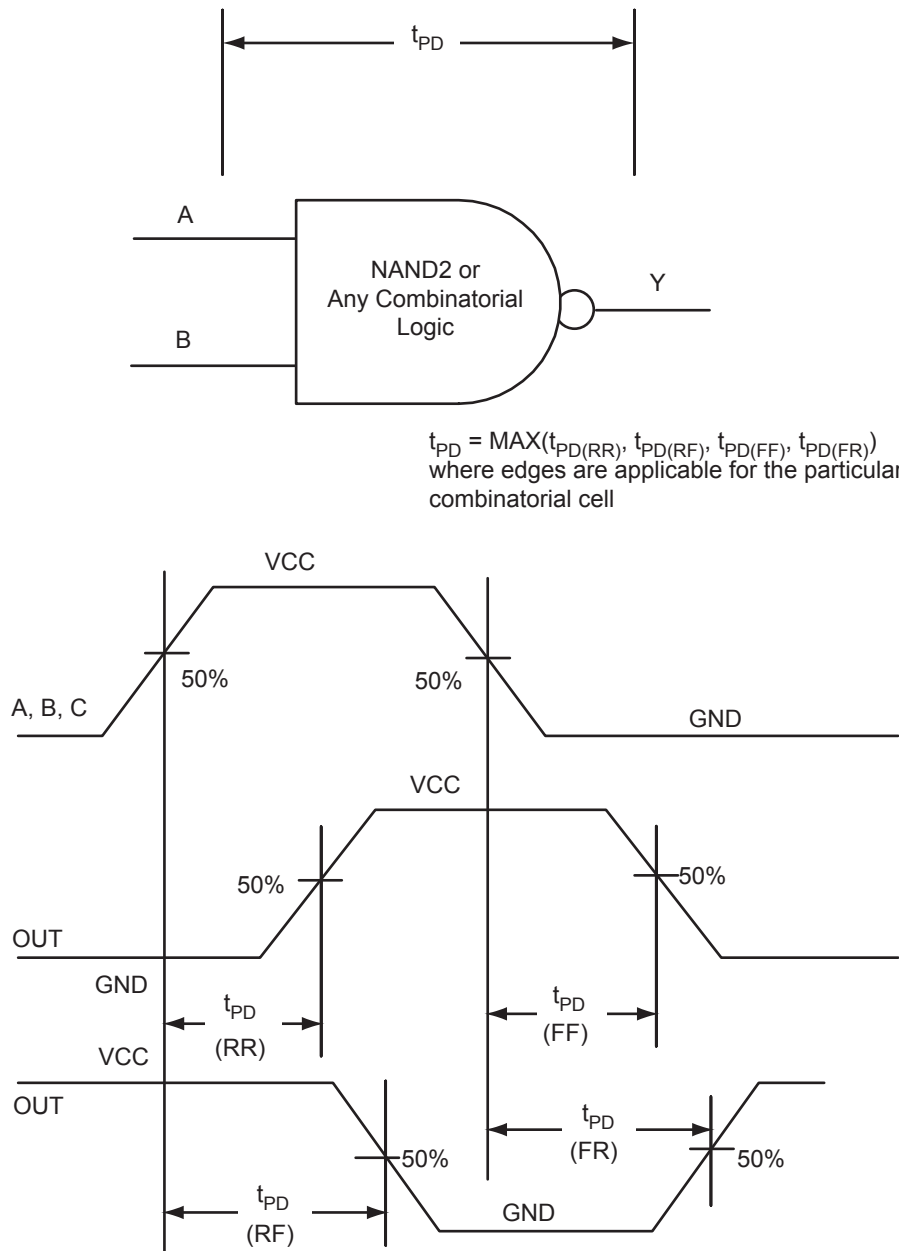


Figure 2-35 • Timing Model and Waveforms

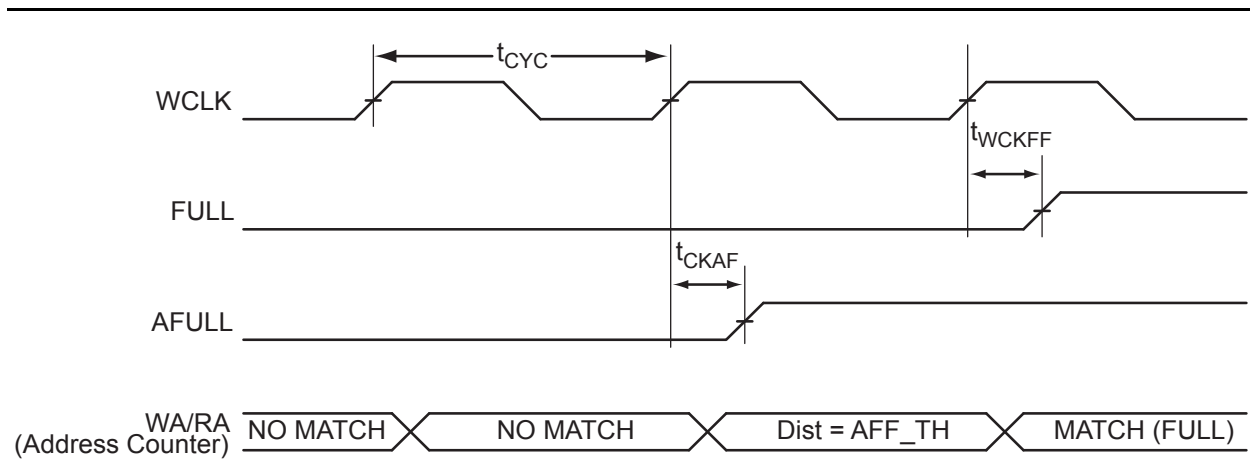


Figure 2-51 • FIFO FULL Flag and AFULL Flag Assertion

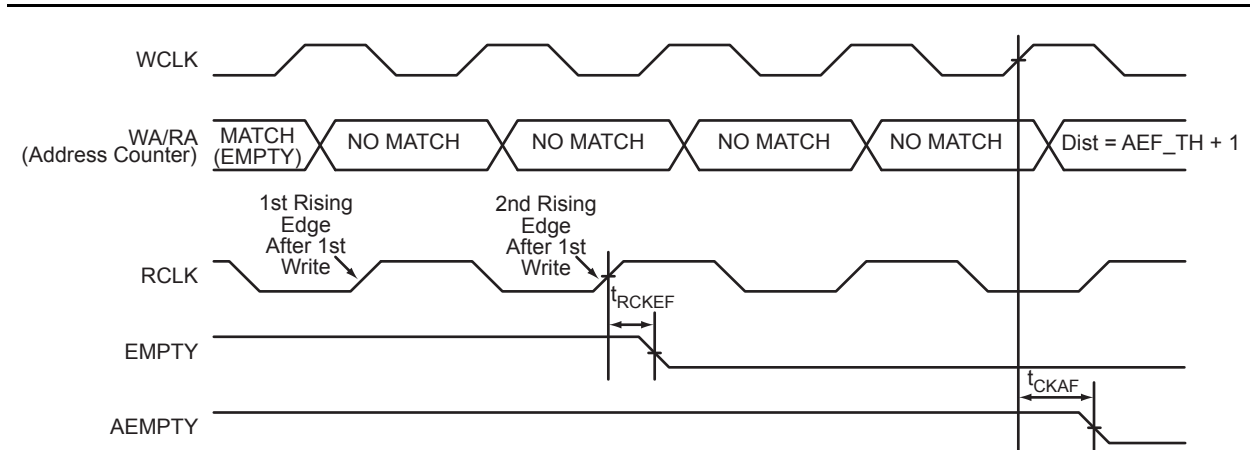


Figure 2-52 • FIFO EMPTY Flag and AEMPTY Flag Deassertion

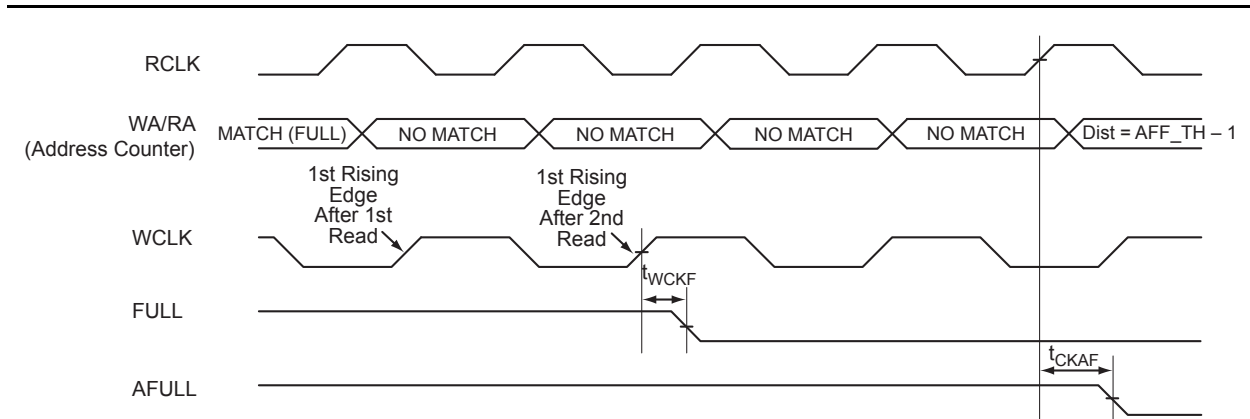


Figure 2-53 • FIFO FULL Flag and AFULL Flag Deassertion

VJTAG

JTAG Supply Voltage

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND. It should be noted that VCC is required to be powered for JTAG operation; VJTAG alone is insufficient. If a device is in a JTAG chain of interconnected boards, the board containing the device can be powered down, provided both VJTAG and VCC to the part remain powered; otherwise, JTAG signals will not be able to transition the device, even in bypass mode.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

VPUMP

Programming Supply Voltage

For programming, VPUMP should be 3.3 V nominal. During normal device operation, VPUMP can be left floating or can be tied (pulled up) to any voltage between 0 V and the VPUMP maximum. Programming power supply voltage (VPUMP) range is listed in the datasheet.

When the VPUMP pin is tied to ground, it will shut off the charge pump circuitry, resulting in no sources of oscillation from the charge pump circuitry.

For proper programming, 0.01 μ F and 0.33 μ F capacitors (both rated at 16 V) are to be connected in parallel across VPUMP and GND, and positioned as close to the FPGA pins as possible.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

User-Defined Supply Pins

VREF

I/O Voltage Reference

Reference voltage for I/O minibanks. VREF pins are configured by the user from regular I/Os, and any I/O in a bank, except JTAG I/Os, can be designated the voltage reference I/O. Only certain I/O standards require a voltage reference—HSTL (I) and (II), SSTL2 (I) and (II), SSTL3 (I) and (II), and GTL/GTL+. One VREF pin can support the number of I/Os available in its minibank.

User Pins

I/O

User Input/Output

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Input and output signal levels are compatible with the I/O standard selected.

During programming, I/Os become tristated and weakly pulled up to VCCI. With VCCI, VMV, and VCC supplies continuously powered up, when the device transitions from programming to operating mode, the I/Os are instantly configured to the desired user configuration.

Unused I/Os are configured as follows:

- Output buffer is disabled (with tristate value of high impedance)
- Input buffer is disabled (with tristate value of high impedance)
- Weak pull-up is programmed

GL

Globals

GL I/Os have access to certain clock conditioning circuitry (and the PLL) and/or have direct access to the global network (spines). Additionally, the global I/Os can be used as regular I/Os, since they have identical capabilities. Unused GL pins are configured as inputs with pull-up resistors.

See more detailed descriptions of global I/O connectivity in the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" chapter of the *ProASIC3E FPGA Fabric User's Guide*. All inputs labeled GC/GF are direct inputs into the quadrant clocks. For example, if GAA0 is used for an input, GAA1 and GAA2 are no longer available for input to the quadrant globals. All inputs labeled GC/GF are direct inputs into the chip-level globals, and the rest are connected to the quadrant globals. The inputs to the global network are multiplexed, and only one input can be used as a global input.

PQ208	
Pin Number	A3PE600 Function
108	TDO
109	TRST
110	VJTAG
111	VMV3
112	GDA0/IO67NPB3V1
113	GDB0/IO66NPB3V1
114	GDA1/IO67PPB3V1
115	GDB1/IO66PPB3V1
116	GDC0/IO65NDB3V1
117	GDC1/IO65PDB3V1
118	IO62NDB3V1
119	IO62PDB3V1
120	IO58NDB3V0
121	IO58PDB3V0
122	GND
123	VCCIB3
124	GCC2/IO55PSB3V0
125	GCB2/IO54PSB3V0
126	NC
127	IO53NDB3V0
128	GCA2/IO53PDB3V0
129	GCA1/IO52PPB3V0
130	GND
131	VCCPLC
132	GCA0/IO52NPB3V0
133	VCOMPLC
134	GCB0/IO51NDB2V1
135	GCB1/IO51PDB2V1
136	GCC1/IO50PSB2V1
137	IO49NDB2V1
138	IO49PDB2V1
139	IO48PSB2V1
140	VCCIB2
141	GND
142	VCC
143	IO47NDB2V1

PQ208	
Pin Number	A3PE600 Function
144	IO47PDB2V1
145	IO44NDB2V1
146	IO44PDB2V1
147	IO43NDB2V0
148	IO43PDB2V0
149	IO40NDB2V0
150	IO40PDB2V0
151	GBC2/IO38PSB2V0
152	GBA2/IO36PSB2V0
153	GBB2/IO37PSB2V0
154	VMV2
155	GNDQ
156	GND
157	VMV1
158	GNDQ
159	GBA1/IO35PDB1V1
160	GBA0/IO35NDB1V1
161	GBB1/IO34PDB1V1
162	GND
163	GBB0/IO34NDB1V1
164	GBC1/IO33PDB1V1
165	GBC0/IO33NDB1V1
166	IO31PDB1V1
167	IO31NDB1V1
168	IO27PDB1V0
169	IO27NDB1V0
170	VCCIB1
171	VCC
172	IO23PPB1V0
173	IO22PSB1V0
174	IO23NPB1V0
175	IO21PDB1V0
176	IO21NDB1V0
177	IO19PPB0V2
178	GND
179	IO18PPB0V2

PQ208	
Pin Number	A3PE600 Function
180	IO19NPB0V2
181	IO18NPB0V2
182	IO17PPB0V2
183	IO16PPB0V2
184	IO17NPB0V2
185	IO16NPB0V2
186	VCCIB0
187	VCC
188	IO15PDB0V2
189	IO15NDB0V2
190	IO13PDB0V2
191	IO13NDB0V2
192	IO11PSB0V1
193	IO09PDB0V1
194	IO09NDB0V1
195	GND
196	IO07PDB0V1
197	IO07NDB0V1
198	IO05PDB0V0
199	IO05NDB0V0
200	VCCIB0
201	GAC1/IO02PDB0V0
202	GAC0/IO02NDB0V0
203	GAB1/IO01PDB0V0
204	GAB0/IO01NDB0V0
205	GAA1/IO00PDB0V0
206	GAA0/IO00NDB0V0
207	GNDQ
208	VMV0

FG484	
Pin Number	A3PE600 Function
N17	IO57NPB3V0
N18	IO55NPB3V0
N19	IO57PPB3V0
N20	NC
N21	IO56NDB3V0
N22	IO58PDB3V0
P1	NC
P2	IO111PDB6V1
P3	IO115NPB6V1
P4	IO113NPB6V1
P5	IO109PPB6V0
P6	IO108PDB6V0
P7	IO108NDB6V0
P8	VCCIB6
P9	GND
P10	VCC
P11	VCC
P12	VCC
P13	VCC
P14	GND
P15	VCCIB3
P16	GDB0/IO66NPB3V1
P17	IO60NDB3V1
P18	IO60PDB3V1
P19	IO61PDB3V1
P20	NC
P21	IO59PDB3V0
P22	IO58NDB3V0
R1	NC
R2	IO110PDB6V0
R3	VCC
R4	IO109NPB6V0
R5	IO106NDB6V0
R6	IO106PDB6V0
R7	GEC0/IO104NPB6V0
R8	VMV5

FG484	
Pin Number	A3PE600 Function
R9	VCCIB5
R10	VCCIB5
R11	IO84NDB5V0
R12	IO84PDB5V0
R13	VCCIB4
R14	VCCIB4
R15	VMV3
R16	VCCPLD
R17	GDB1/IO66PPB3V1
R18	GDC1/IO65PDB3V1
R19	IO61NDB3V1
R20	VCC
R21	IO59NDB3V0
R22	IO62PDB3V1
T1	NC
T2	IO110NDB6V0
T3	NC
T4	IO105PDB6V0
T5	IO105NDB6V0
T6	GEC1/IO104PPB6V0
T7	VCOMPLE
T8	GNDQ
T9	GEA2/IO101PPB5V2
T10	IO92NDB5V1
T11	IO90NDB5V1
T12	IO82NDB5V0
T13	IO74NDB4V1
T14	IO74PDB4V1
T15	GNDQ
T16	VCOMPLD
T17	VJTAG
T18	GDC0/IO65NDB3V1
T19	GDA1/IO67PDB3V1
T20	NC
T21	IO64PDB3V1
T22	IO62NDB3V1

FG484	
Pin Number	A3PE600 Function
U1	NC
U2	IO107PDB6V0
U3	IO107NDB6V0
U4	GEB1/IO103PDB6V0
U5	GEB0/IO103NDB6V0
U6	VMV6
U7	VCCPLE
U8	IO101NPB5V2
U9	IO95PPB5V1
U10	IO92PDB5V1
U11	IO90PDB5V1
U12	IO82PDB5V0
U13	IO76NDB4V1
U14	IO76PDB4V1
U15	VMV4
U16	TCK
U17	VPUMP
U18	TRST
U19	GDA0/IO67NDB3V1
U20	NC
U21	IO64NDB3V1
U22	IO63PDB3V1
V1	NC
V2	NC
V3	GND
V4	GEA1/IO102PDB6V0
V5	GEA0/IO102NDB6V0
V6	GNDQ
V7	GEC2/IO99PDB5V2
V8	IO95NPB5V1
V9	IO91NDB5V1
V10	IO91PDB5V1
V11	IO83NDB5V0
V12	IO83PDB5V0
V13	IO77NDB4V1
V14	IO77PDB4V1

FG484	
Pin Number	A3PE600 Function
V15	IO69NDB4V0
V16	GDB2/IO69PDB4V0
V17	TDI
V18	GNDQ
V19	TDO
V20	GND
V21	NC
V22	IO63NDB3V1
W1	NC
W2	NC
W3	NC
W4	GND
W5	IO100NDB5V2
W6	GEB2/IO100PDB5V2
W7	IO99NDB5V2
W8	IO88NDB5V0
W9	IO88PDB5V0
W10	IO89NDB5V0
W11	IO80NDB4V1
W12	IO81NDB4V1
W13	IO81PDB4V1
W14	IO70NDB4V0
W15	GDC2/IO70PDB4V0
W16	IO68NDB4V0
W17	GDA2/IO68PDB4V0
W18	TMS
W19	GND
W20	NC
W21	NC
W22	NC
Y1	VCCIB6
Y2	NC
Y3	NC
Y4	IO98NDB5V2
Y5	GND
Y6	IO94NDB5V1

FG484	
Pin Number	A3PE600 Function
Y7	IO94PDB5V1
Y8	VCC
Y9	VCC
Y10	IO89PDB5V0
Y11	IO80PDB4V1
Y12	IO78NPB4V1
Y13	NC
Y14	VCC
Y15	VCC
Y16	NC
Y17	NC
Y18	GND
Y19	NC
Y20	NC
Y21	NC
Y22	VCCIB3

FG676	
Pin Number	A3PE1500 Function
R21	IO89NDB3V0
R22	GCB2/IO89PDB3V0
R23	IO90NDB3V0
R24	GCC2/IO90PDB3V0
R25	IO91PDB3V0
R26	IO91NDB3V0
T1	IO186PDB6V2
T2	IO185NDB6V2
T3	GNDQ
T4	IO180PDB6V1
T5	IO180NDB6V1
T6	IO188NDB6V2
T7	GFB2/IO188PDB6V2
T8	VCCIB6
T9	VCC
T10	GND
T11	GND
T12	GND
T13	GND
T14	GND
T15	GND
T16	GND
T17	GND
T18	VCC
T19	VCCIB3
T20	IO99PDB3V1
T21	IO99NDB3V1
T22	IO97PDB3V1
T23	IO97NDB3V1
T24	GNDQ
T25	IO93PPB3V0
T26	NC
U1	IO186NDB6V2
U2	IO184NDB6V2
U3	IO184PDB6V2
U4	IO182NDB6V1

FG676	
Pin Number	A3PE1500 Function
U5	IO182PDB6V1
U6	IO178PDB6V1
U7	IO178NDB6V1
U8	VCCIB6
U9	VCC
U10	GND
U11	GND
U12	GND
U13	GND
U14	GND
U15	GND
U16	GND
U17	GND
U18	VCC
U19	VCCIB3
U20	NC
U21	IO101NDB3V1
U22	IO101PDB3V1
U23	IO92NDB3V0
U24	IO92PDB3V0
U25	IO95PDB3V1
U26	IO93NPB3V0
V1	IO183PDB6V2
V2	IO183NDB6V2
V3	VMV6
V4	IO181PDB6V1
V5	IO181NDB6V1
V6	IO176PDB6V1
V7	IO176NDB6V1
V8	VCCIB6
V9	VCC
V10	VCC
V11	VCC
V12	VCC
V13	VCC
V14	VCC

FG676	
Pin Number	A3PE1500 Function
V15	VCC
V16	VCC
V17	VCC
V18	VCC
V19	VCCIB3
V20	IO107PDB3V2
V21	IO107NDB3V2
V22	IO103NDB3V2
V23	IO103PDB3V2
V24	VMV3
V25	IO95NDB3V1
V26	IO94PDB3V0
W1	IO179NDB6V1
W2	IO179PDB6V1
W3	IO177NDB6V1
W4	IO177PDB6V1
W5	IO172PDB6V0
W6	IO172NDB6V0
W7	VCC
W8	VCC
W9	VCCIB5
W10	VCCIB5
W11	VCCIB5
W12	VCCIB5
W13	VCCIB5
W14	VCCIB4
W15	VCCIB4
W16	VCCIB4
W17	VCCIB4
W18	VCCIB4
W19	VCC
W20	VCCIB3
W21	GDB0/IO109NDB3V2
W22	GDB1/IO109PDB3V2
W23	IO105NDB3V2
W24	IO105PDB3V2

Revision	Changes	Page														
Revision 9 (Aug 2009) Product Brief v1.2	All references to speed grade –F have been removed from this document.	N/A														
DC and Switching Characteristics v1.3	The "Pro I/Os with Advanced I/O Standards" section was revised to add definitions of hot-swap and cold-sparing.	1-6														
	3.3 V LVCMOS and 1.2 V LVCMOS Wide Range support was added to the datasheet. This affects all tables that contained 3.3 V LVCMOS and 1.2 V LVCMOS data.	N/A														
	IIL and IIH input leakage current information was added to all "Minimum and Maximum DC Input and Output Levels" tables.	N/A														
	–F was removed from the datasheet. The speed grade is no longer supported.	N/A														
	In the Table 2-2 • Recommended Operating Conditions ¹ "3.0 V DC supply voltage" and note 4 are new.	2-2														
	The Table 2-4 • Overshoot and Undershoot Limits ¹ table was updated.	2-3														
	The Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays table was updated.	2-5														
	There are new parameters and data was updated in the Table 2-99 • RAM4K9 table.	2-76														
	There are new parameters and data was updated in the Table 2-100 • RAM512X18 table.	2-77														
Revision 8 (Feb 2008) Product Brief v1.1	Table 1-2 • ProASIC3E FPGAs Package Sizes Dimensions is new.	1-II														
Revision 7 (Jun 2008) DC and Switching Characteristics v1.2	The title of Table 2-4 • Overshoot and Undershoot Limits ¹ was modified to remove "as measured on quiet I/Os." Table note 2 was revised to remove "estimated SSO density over cycles." Table note 3 was deleted.	2-3														
	Table 2-78 • LVDS Minimum and Maximum DC Input and Output Levels was updated.	2-50														
Revision 6 (Jun 2008)	The A3PE600 "FG484" table was missing G22. The pin and its function were added to the table.	4-27														
Revision 5 (Jun 2008) Packaging v1.4	The naming conventions changed for the following pins in the "FG484" for the A3PE600: <table><tr><th>Pin Number</th><th>New Function Name</th></tr><tr><td>J19</td><td>IO45PPB2V1</td></tr><tr><td>K20</td><td>IO45NPB2V1</td></tr><tr><td>M2</td><td>IO114NPB6V1</td></tr><tr><td>N1</td><td>IO114PPB6V1</td></tr><tr><td>N4</td><td>GFC2/IO115PPB6V1</td></tr><tr><td>P3</td><td>IO115NPB6V1</td></tr></table>	Pin Number	New Function Name	J19	IO45PPB2V1	K20	IO45NPB2V1	M2	IO114NPB6V1	N1	IO114PPB6V1	N4	GFC2/IO115PPB6V1	P3	IO115NPB6V1	4-22
Pin Number	New Function Name															
J19	IO45PPB2V1															
K20	IO45NPB2V1															
M2	IO114NPB6V1															
N1	IO114PPB6V1															
N4	GFC2/IO115PPB6V1															
P3	IO115NPB6V1															
Revision 4 (Apr 2008) Product Brief v1.0	The product brief portion of the datasheet was divided into two sections and given a version number, starting at v1.0. The first section of the document includes features, benefits, ordering information, and temperature and speed grade offerings. The second section is a device family overview.	N/A														
Packaging v1.3	The "FG324" package diagram was replaced.	4-12														